

## NCE N-Channel Enhancement Mode Power MOSFET

### Description

The NCE85H15T uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. This device is suitable for use in PWM, load switching and general purpose applications.

### General Features

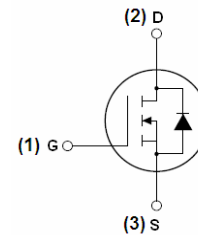
- $V_{DS} = 85V, I_D = 150A$   
 $R_{DS(ON)} < 4.8m\Omega @ V_{GS} = 10V$  (Typ: 3.9m $\Omega$ )
- High density cell design for ultra low  $R_{DS(on)}$
- Fully characterized avalanche voltage and current
- Special designed for Convertors and power controls
- Good stability and uniformity with high  $E_{AS}$
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

### Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

**100% UIS TESTED!**

**100%  $\Delta V_{ds}$  TESTED!**



Schematic diagram



Marking and pin assignment



TO-247 top view

### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE85H15T	NCE85H15T	TO-247	-	-	-

### Absolute Maximum Ratings ( $T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	85	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	150	A
Drain Current-Continuous( $T_C = 100^\circ C$ )	$I_D(100^\circ C)$	106	A
Pulsed Drain Current	$I_{DM}$	600	A
Maximum Power Dissipation	$P_D$	270	W
Peak diode recovery voltage	dv/dt	15	V/ns
Derating factor		1.8	W/ $^\circ C$
Single pulse avalanche energy <sup>(Note 5)</sup>	$E_{AS}$	1100	mJ

Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 175	°C
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## Thermal Characteristic

Thermal Resistance, Junction-to-Case <sup>(Note 2)</sup>	$R_{\theta JC}$	0.56	°C/W
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## Electrical Characteristics ( $T_C=25^\circ\text{C}$ unless otherwise noted)

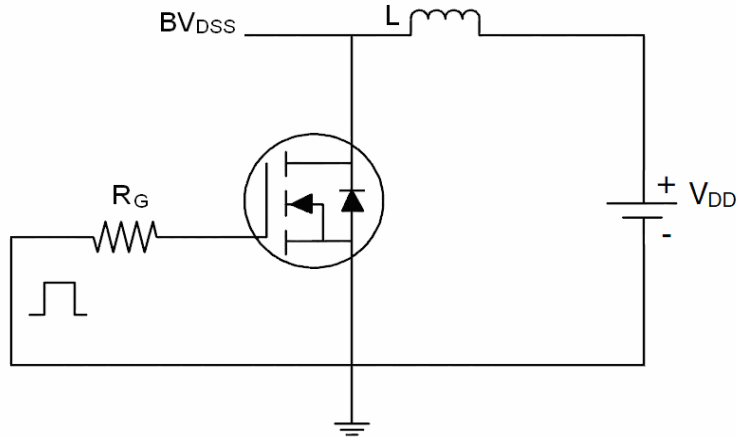
Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	85	89	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=85V, V_{GS}=0V$	-	-	1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 100$	nA
<b>On Characteristics</b> <sup>(Note 3)</sup>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2	2.85	4	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=40A$	-	3.9	4.8	m $\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS}=25V, I_D=40A$	110	-	-	S
<b>Dynamic Characteristics</b> <sup>(Note 4)</sup>						
Input Capacitance	$C_{iss}$	$V_{DS}=25V, V_{GS}=0V,$ $F=1.0MHz$	-	8800	-	PF
Output Capacitance	$C_{oss}$		-	680	-	PF
Reverse Transfer Capacitance	$C_{rss}$		-	520	-	PF
<b>Switching Characteristics</b> <sup>(Note 4)</sup>						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=30V, I_D=2A, R_L=15\Omega$ $, R_G=2.5\Omega, V_{GS}=10V$	-	22.5	-	nS
Turn-on Rise Time	$t_r$		-	15	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	70	-	nS
Turn-Off Fall Time	$t_f$		-	18.75	-	nS
Total Gate Charge	$Q_g$	$V_{DS}=30V, I_D=30A,$ $V_{GS}=10V$	-	200	-	nC
Gate-Source Charge	$Q_{gs}$		-	40	-	nC
Gate-Drain Charge	$Q_{gd}$		-	60	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage <sup>(Note 3)</sup>	$V_{SD}$	$V_{GS}=0V, I_S=40A$	-	-	1.2	V
Diode Forward Current <sup>(Note 2)</sup>	$I_S$		-	-	150	A
Reverse Recovery Time	$t_{rr}$	$T_J=25^\circ\text{C}, I_F=75A$ $di/dt=100A/\mu s$ <sup>(Note 3)</sup>	-		45	nS
Reverse Recovery Charge	$Q_{rr}$		-		70	nC
Forward Turn-On Time	$t_{on}$	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

## Notes:

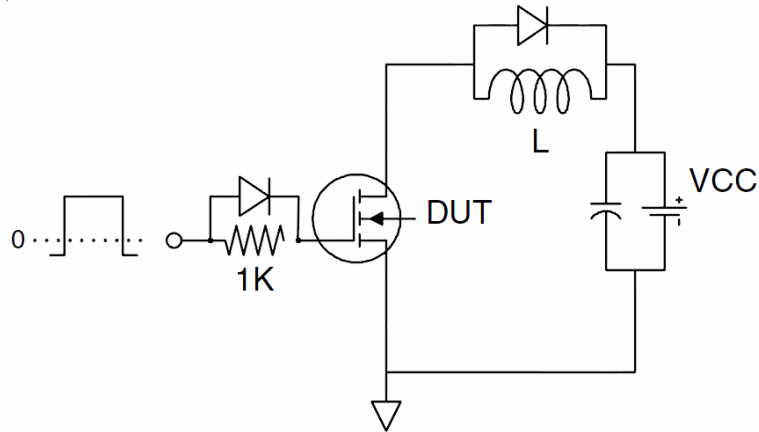
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production
5. EAS condition:  $T_J=25^\circ\text{C}, V_{DD}=42.5V, V_G=10V, L=0.5mH, R_g=25\Omega$

## Test Circuit

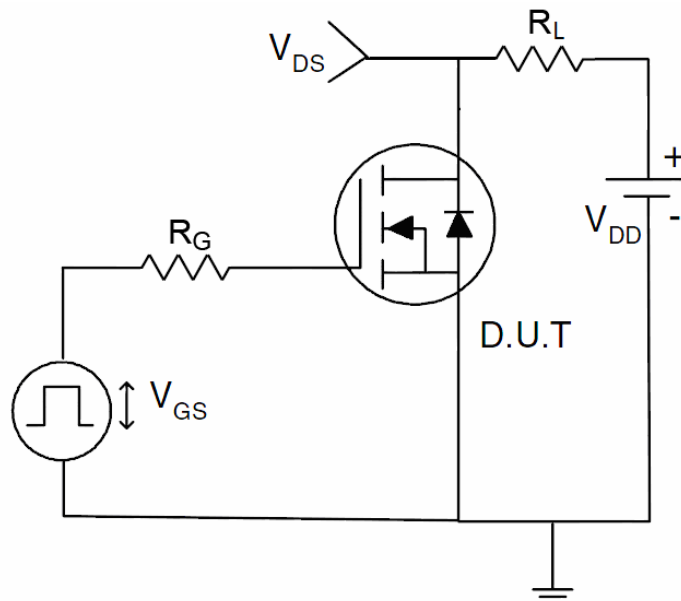
### 1) $E_{AS}$ test Circuits



### 2) Gate charge test Circuit:



### 3) Switch Time Test Circuit:



Typical Electrical and Thermal Characteristics (Curves)

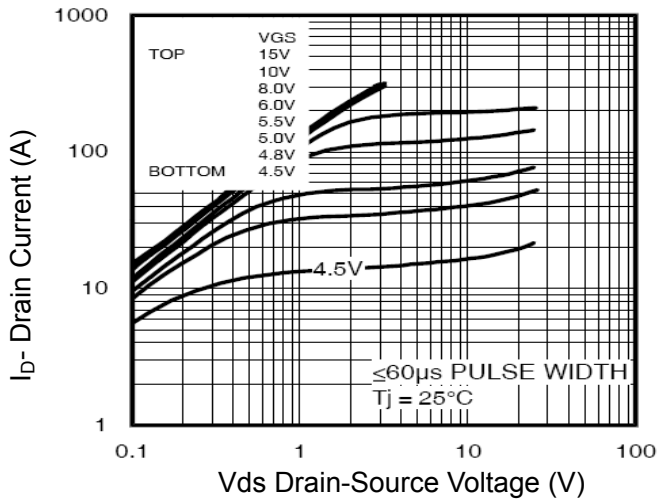


Figure 1 Output Characteristics

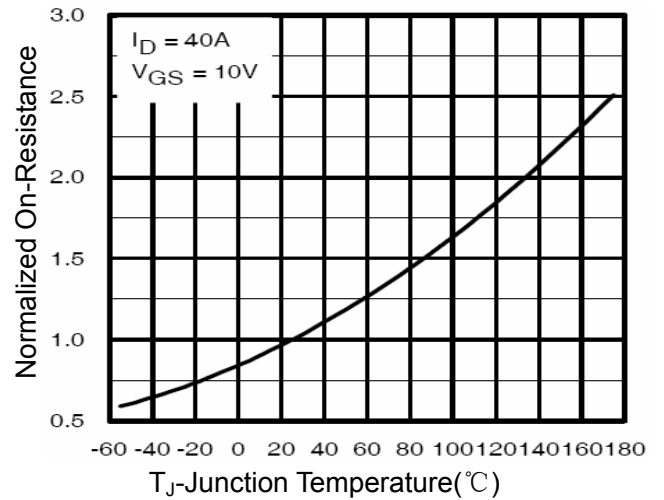


Figure 4 Rdson-Junction Temperature

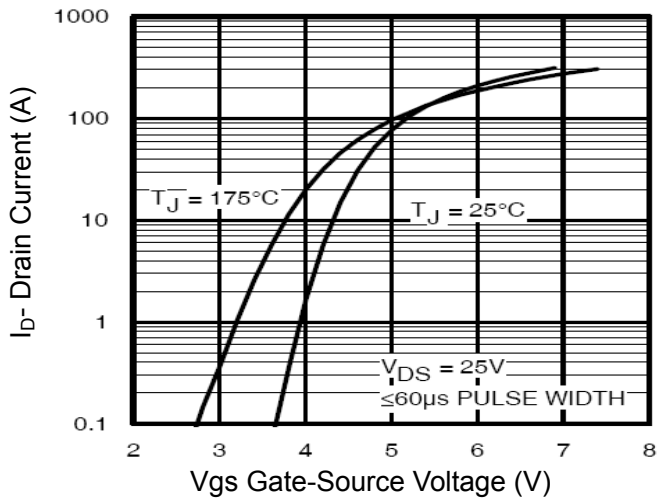


Figure 2 Transfer Characteristics

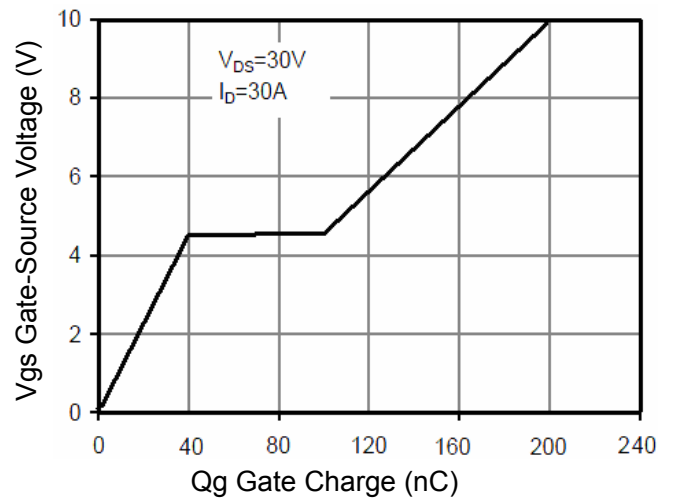


Figure 5 Gate Charge

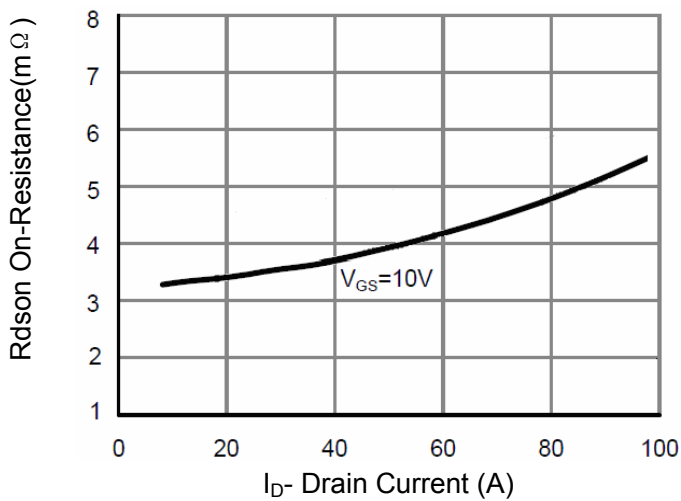


Figure 3 Rdson- Drain Current

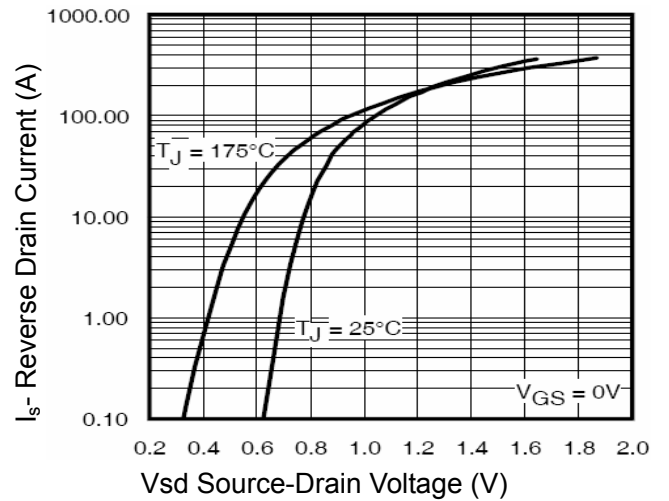


Figure 6 Source- Drain Diode Forward

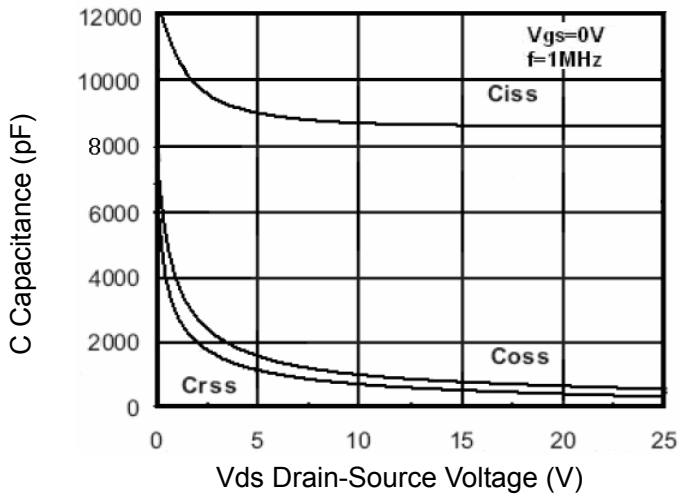


Figure 7 Capacitance vs Vds

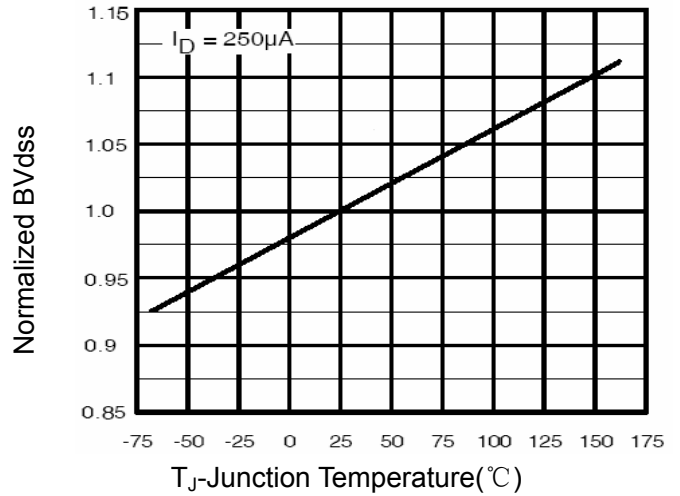


Figure 9  $BV_{DSS}$  vs Junction Temperature

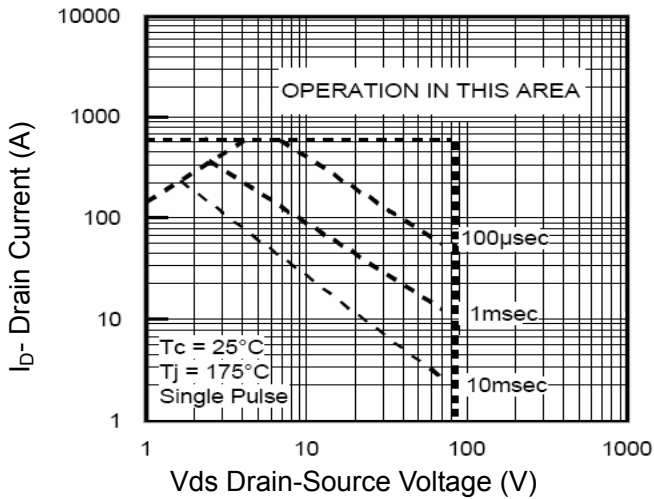


Figure 8 Safe Operation Area

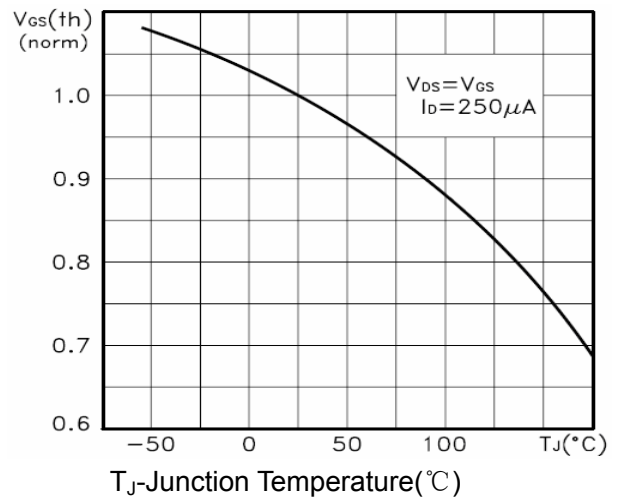


Figure 10  $V_{GS(th)}$  vs Junction Temperature

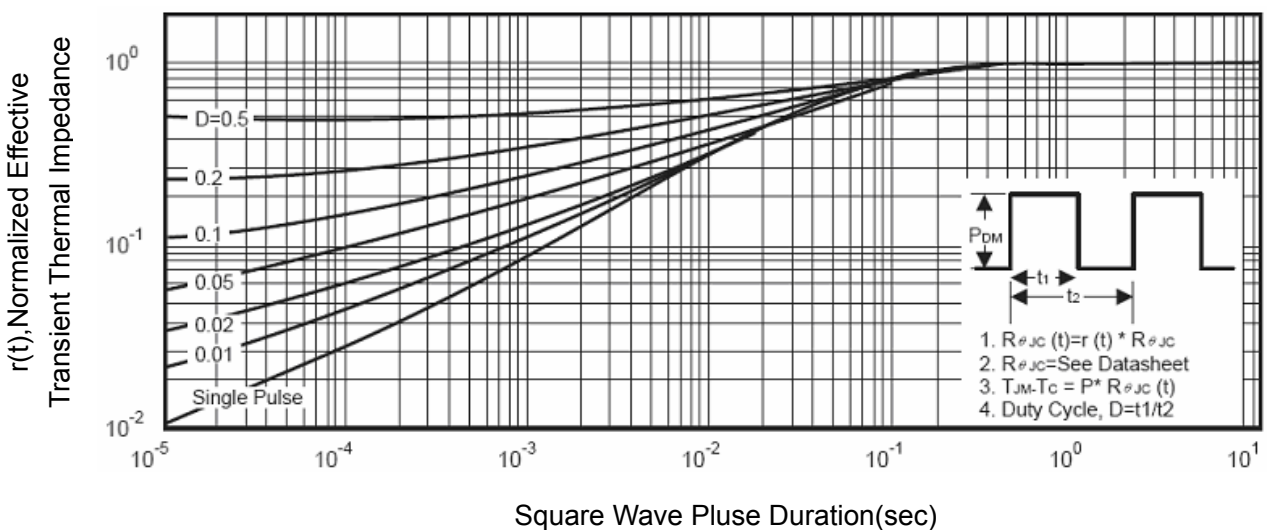
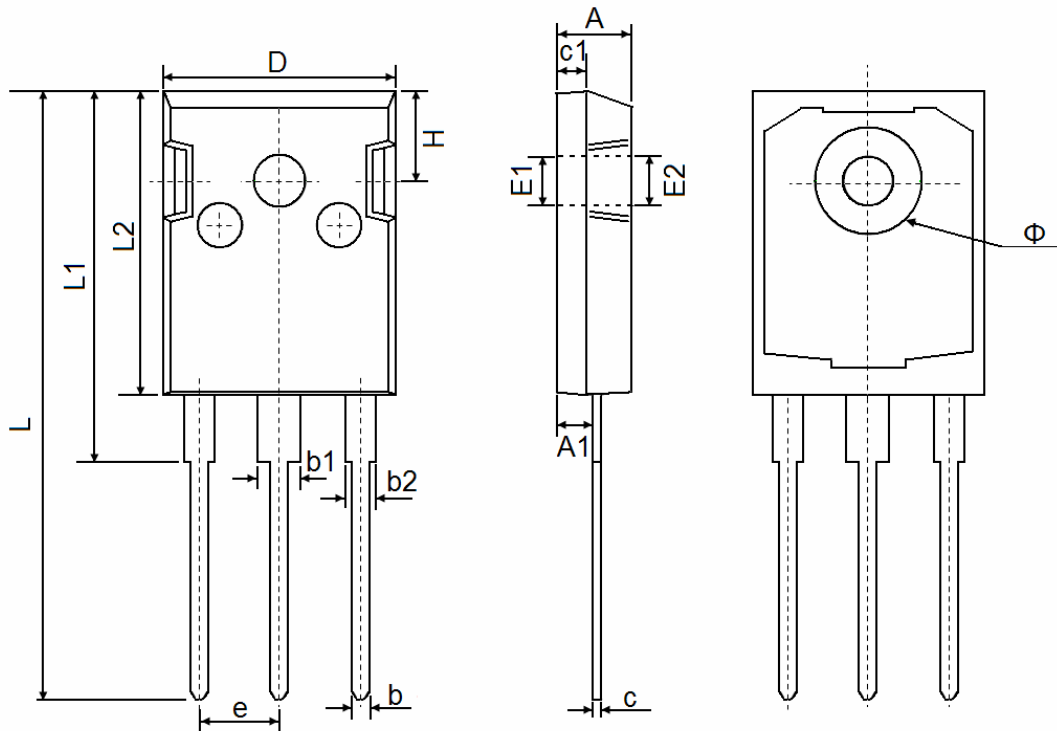


Figure 11 Normalized Maximum Transient Thermal Impedance

**TO-247 Package Information**


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.850	5.150	0.191	0.200
A1	2.200	2.600	0.087	0.102
b	1.000	1.400	0.039	0.055
b1	2.800	3.200	0.110	0.126
b2	1.800	2.200	0.071	0.087
c	0.500	0.700	0.020	0.028
c1	1.900	2.100	0.075	0.083
D	15.450	15.750	0.608	0.620
E1	3.500 REF		0.138 REF	
E2	3.600 REF		0.142 REF	
L	40.900	41.300	1.610	1.626
L1	24.800	25.100	0.976	0.988
L2	20.300	20.600	0.799	0.811
Φ	7.100	7.300	0.280	0.287
e	5.450 TYP		0.215 TYP	
H	5.980 REF		0.235 REF	

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